

a reflective pixel electrode formed on said interlayer insulating film wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer.

[wherein said two conductive layers are electrically connected to each other with said embedded conductive layer, and

wherein said embedded conductive layer comprises an organic resin film containing a conductive material dispersed therein or an inorganic film containing a conductive material dispersed therein.]

2. (Amended) A semiconductor device comprising:

[two conductive layers provided as separate layers;
an insulating layer sandwiched by said two conductive layers; and
an oxide conductive layer provided to fill an opening formed in said insulating layer,

wherein said two conductive layers are electrically connected to each other with said oxide conductive layer.]

at least one transistor;

at least one interlayer insulating film comprising an organic resin formed over said transistor, said interlayer insulating film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer.

3. (Amended) A semiconductor device comprising:

[two conductive layers provided as separate layers;
an insulating layer sandwiched by said two conductive layers; and

an embedded conductive layer provided to fill an opening formed in said insulating layer,

wherein said two conductive layers are electrically connected to each other with said embedded conductive layer,

wherein said embedded conductive layer comprises an organic resin film containing a conductive material dispersed therein or an inorganic film containing a conductive material therein, and

wherein a shape of said opening is in accordance with a shape of said embedded conductive layer embedded in said opening]

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film formed over said capacitor forming electrode and said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said embedded conductive layer.

4. (Amended) A semiconductor device comprising:

[two conductive layers provided as separate layers;

an insulating layer sandwiched by said two conductive layers; and

an oxide conductive layer provided to fill an opening formed in said insulating layer,

wherein said two conductive layers are electrically connected to each other with said oxide conductive layer, and

wherein a shape of said opening is in accordance with a shape of said oxide conductive layer embedded in said opening]

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film comprising an organic resin formed over said capacitor forming electrode and said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said embedded conductive layer.

5. (Amended) A semiconductor device comprising:

[two conductive layers provided as separate layers;

an insulating layer sandwiched by said two conductive layers; and

an embedded conductive layer provided to fill an opening formed in said insulating layer,

wherein said two conductive layers are electrically connected to each other with said embedded conductive layer,

wherein said embedded conductive layer comprises an organic resin film containing a conductive material dispersed therein or an inorganic film containing a conductive material dispersed therein, and

wherein one of said two conductive layers is provided on a flat surface formed by said embedded conductive layer]

at least one transistor;

at least one interlayer insulating film comprising an organic resin formed over said transistor, said interlayer film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer,

wherein said embedded conductive layer comprises a same resin as said resin of the interlayer insulating film.

6. (Amended) A semiconductor device comprising:

[two conductive layers provided as separate layers;

an insulating layer sandwiched by said two conductive layers; and

an oxide conductive layer provided to fill an opening formed in said insulating layer,

wherein said two conductive layers are electrically connected to each other with said oxide conductive layer, and

wherein one of said two conductive layers is provided on a flat surface formed by said oxide conductive layer]

at least one transistor;

at least one interlayer insulating film comprising an organic resin formed over said transistor, said interlayer insulating film having at least one contact hole;

a conductive layer formed on said interlayer insulating film wherein said conductive layer extends into said contact hole and electrically connected to said transistor; and

a reflective pixel electrode formed on said conductive layer, wherein at least one peripheral edge of said reflective pixel electrode is coextensive with a peripheral edge of said conductive layer.

7. (Amended) A semiconductor device according to any one of claim 1 to 5, wherein said embedded conductive layer comprises carbon dispersed in an organic or inorganic material [conductive material is a carbon material].

8. (Amended) ~~A semiconductor device~~ according to any one of claim [3] 1 to 5, wherein said embedded conductive layer comprises zinc oxide, aluminum flakes or nickel flakes dispersed in an organic or inorganic material [conductive material is a carbon material].

9. (Amended) A semiconductor device according to claim [5] 6, wherein said conductive [material is carbon material] layer comprises carbon dispersed in an organic or inorganic material.

10. (Amended) A semiconductor device according to claim [1] 6, wherein said conductive layer comprises a material [is] selected from the group consisting of zinc oxide, aluminum flakes and nickel flakes.

13. (Amended) A semiconductor device according to any one of claim [2] 1 to 5, wherein said embedded conductive layer comprises an oxide conductive material [layer comprises indium tin oxide].

14. (Amended) A semiconductor device according to claim [4] 13, wherein said oxide conductive [layer] material comprises indium tin oxide.

15. (Amended) A semiconductor device according to claim 6 wherein said [oxide] conductive layer comprises a conductive oxide material [indium tin oxide].

16. (Amended) A semiconductor device according to any one of claims 1 to 6,
[wherein one of said two conductive layers is in contact with] further comprising an alignment
film.

22. (Amended) A semiconductor device according to claim 1, 2, 3, 4, 5 or 6 [is
applied to] wherein said device is a display device of a cellular phone.

23. (Amended) A semiconductor device according to claim 1, 2, 3, 4, 5 or 6 [is
applied to] wherein said device is a display device of a camcorder.

24. (Amended) A semiconductor device according to claim 1, 2, 3, 4, 5 or 6 [is
applied to] wherein said device is a display device of a portable computer.

25. (Amended) A semiconductor device according to claim 1, 2, 3, 4, 5 or 6 [is
applied to] wherein said device is a display device of a head mounting display.

26. (Amended) A semiconductor device according to claim 1, 2, 3, 4, 5 or 6 [is
applied to] wherein said device is a display device of a rear type projector.

27. (Amended) A semiconductor device according to claim 1, 2, 3, 4, 5, or 6 [is
applied to] wherein said device is a display device of a front type projector.

40. (Amended) A semiconductor device according to any one of claim 1 to 6 [is
applied to] wherein said device is an EL display device.

Please add new claim 46 as follows:

--46. The semiconductor device according to claim 5 wherein said third interlayer
insulating film and said embedded conductive layer both comprises an acrylic resin.--